

# SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

NPN Epitaxial Planar Silicon Transistor

# 15C01SS — Low-Frequency General-Purpose Amplifier Applications

## **Applications**

· Low-frequency Amplifier, muting circuit

#### **Features**

- · Large current capacity
- · Low collector-to-emitter saturation voltage (resistance): R<sub>CE</sub>(sat) typ=0.58Ω [I<sub>C</sub>=0.7A, I<sub>B</sub>=35mA]
- · Ultrasmall, slim flat-lead package (1.4mm×0.8mm×0.6mm)
- · Small ON-resistance (Ron)

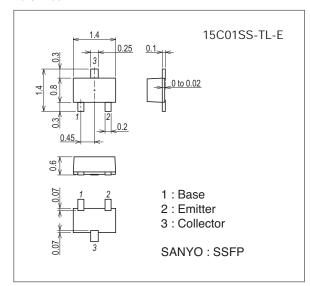
#### **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		20	V
Collector-to-Emitter Voltage	VCEO		15	V
Emitter-to-Base Voltage	V <sub>EBO</sub>		5	V
Collector Current	IC		600	mA
Collector Current (Pulse)	ICP		1.2	Α
Collector Dissipation	PC	Mounted on a glass epoxy board (20×30×1.6mm)	200	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### **Package Dimensions**

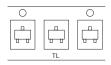
unit : mm (typ) 7029A-002



#### **Product & Package Information**

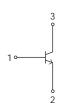
Package : SSFP
 JEITA, JEDEC : SC-81
 Minimum Packing Quantity : 8,000 pcs./reel

#### Packing Type: TL Marking





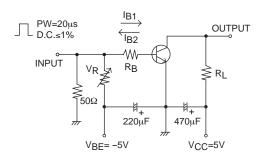
#### **Electrical Connection**



#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
	Symbol	Conditions	min	typ	max	Unit
Collector Cutoff Current	ICBO	V <sub>CB</sub> =15V, I <sub>E</sub> =0A			0.1	μА
Emitter Cutoff Current	IEBO	V <sub>EB</sub> =4V, I <sub>C</sub> =0A			0.1	μΑ
DC Current Gain	hFE	V <sub>CE</sub> =2V, I <sub>C</sub> =10mA	300		800	
Gain-Bandwidth Product	fT	V <sub>CE</sub> =2V, I <sub>C</sub> =50mA		330		MHz
Output Capacitance	Cob	V <sub>CB</sub> =10V, f=1MHz		3.2		pF
Collector-to-Emitter Saturation Voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> =200mA, I <sub>B</sub> =10mA		150	300	mV
Base-to-Emitter Saturation Voltage	V <sub>BE</sub> (sat)	I <sub>C</sub> =200mA, I <sub>B</sub> =10mA		0.9	1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =10μA, I <sub>E</sub> =0A	20			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=1mA, RBE=∞	15			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	IE=10μA, IC=0A	5			V
Turn-ON Time	ton			30		ns
Storage Time	tstg	See specified Test Circuit.		77		ns
Fall Time	tf			40		ns

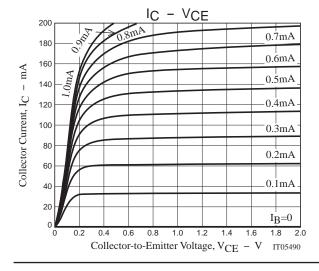
### **Switching Time Test Circuit**

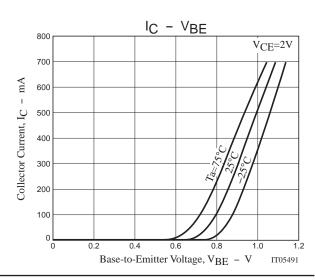


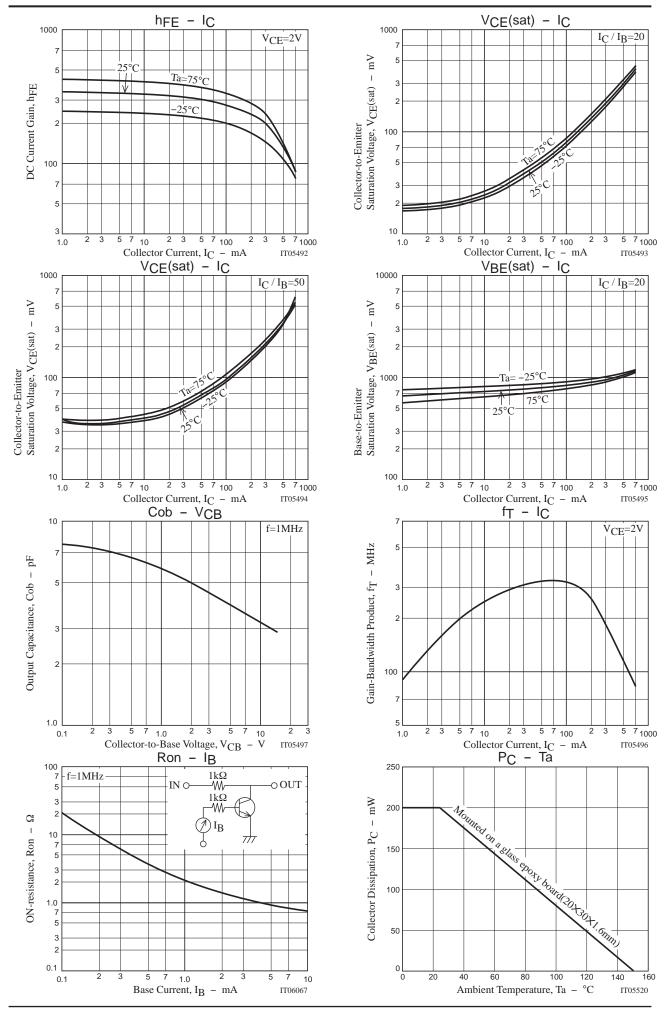
 $I_{C}=20I_{B1}=-20I_{B2}=500mA$ 

### **Ordering Information**

Device	Package	Shipping	memo	
15C01SS-TL-E			Pb Free	





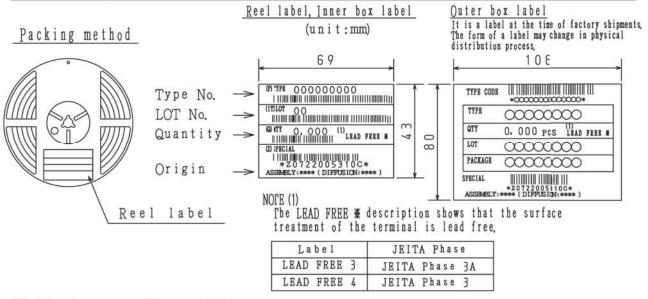


#### **Embossed Taping Specification**

15C01SS-TL-E

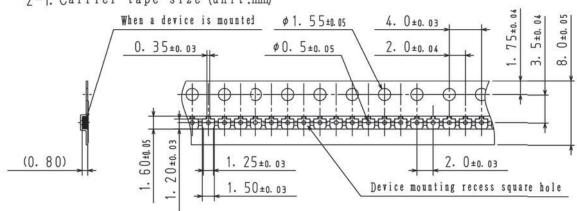
#### 1. Packing Format

Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing format		
	Туре	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)	
SSFP	SSFP	8, 000	40,000	240, 000	5 reels contained Dimensions:mm (external)	6 inner boxes contained Dimension::mm (external)	
					183×72×185	440×195×210	

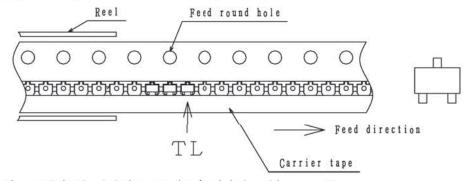


# 2. Taping configuration

2-1. Carrier tape size (unit:mm)



#### 2-2. Device placement direction



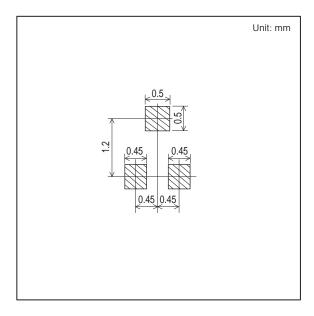
Those with pin 1 index on the feed hole side ······TL

# **Outline Drawing**

15C01SS-TL-E

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# Land Pattern Example



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